

MEMORY CIRCUIT HAVING BLOCK ADDRESS SWITCHING FUNCTION

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Applicant: FUJITSU LTD

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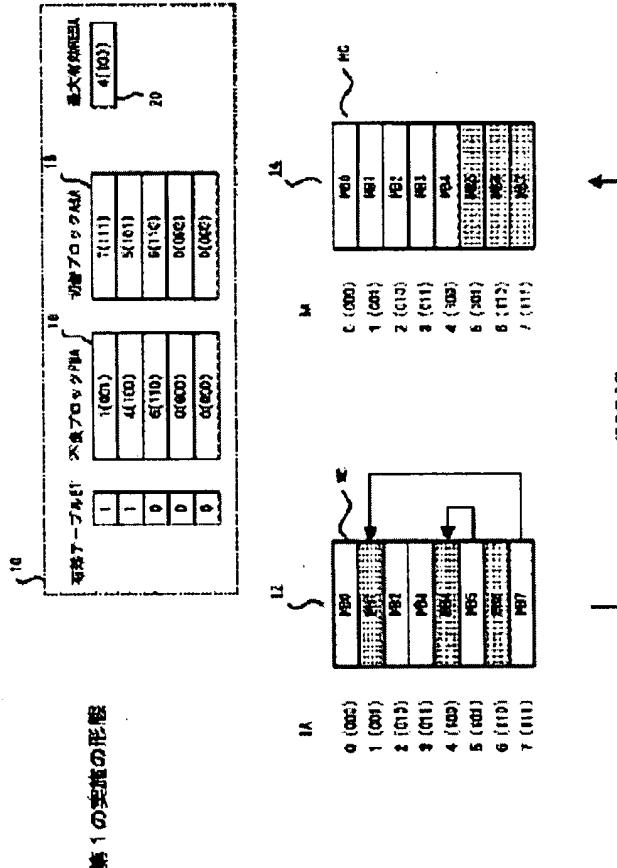
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Abstract of JP2003045196

PROBLEM TO BE SOLVED: To relieve a defective memory cell by using effectively a memory cell region in a chip and to enable accessing by varying sequentially an address from the outside even when relieving the defective memory cell. **SOLUTION:** In a memory circuit in which a defective cell can be relieved, the circuit has a plurality of memory blocks MB having respectively a plurality of memory cells, a region 16 storing a block address of a defective memory block having a defective cell, and a comparison circuit comparing a block address to be accessed with a block address of a defective memory block and detecting access to the defective memory block. And when the comparison circuit detects access to the defective memory block, the defective memory block is replaced by a memory block of the highest order address (or the lowest order address) out of a plurality of the memory blocks. When a plurality of defective memory blocks exist, they are replaced successively from the most significant bit (or the least significant bit) as switching memory blocks.



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(54) MEMORY CIRCUIT HAVING BLOCK ADDRESS SWITCHING FUNCTION

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